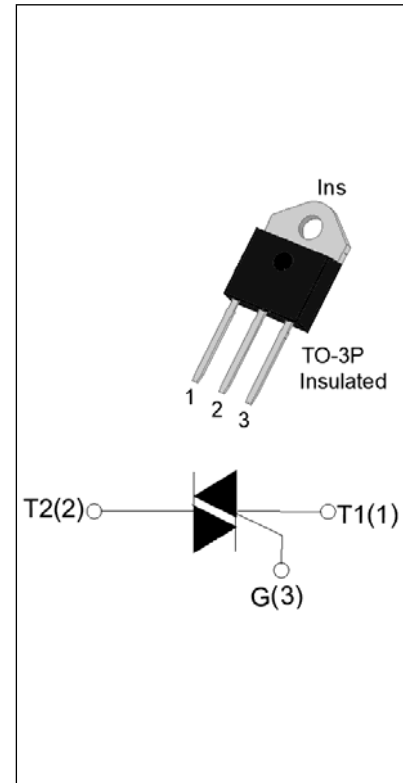


**JST26Z-800BW 25A TRIAC**

Rev.A.1.0

**DESCRIPTION:**

The JST26Z-800BW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST26Z-800BW snubberless triac is especially recommended for use on inductive loads. By using an internal ceramic pad, JST26Z-800BW provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-3P is RoHS compliant.


**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	25	A
$V_{DRM}/V_{RRM}$	800	V
$I_{GT\ I/II/III}$	50/50/50	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	°C
Operating junction temperature range	$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{DRM}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{RRM}$	800	V
RMS on-state current ( $T_c \leq 86^\circ\text{C}$ )	$I_{T(RMS)}$	25	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{TSM}$	250	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		275	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	340	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	$di/dt$	100	$\text{A}/\mu\text{s}$
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )	$I_{GM}$	4	A
Average gate power dissipation ( $T_j=125^\circ\text{C}$ )	$P_{G(AV)}$	0.5	W

Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25^\circ\text{C}$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	5	kV

**ELECTRICAL CHARACTERISTICS**( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12\text{V } R_L=33\Omega$	I - II -III	MAX.	50	mA
$V_{GT}$		I - II -III	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I -III	MAX.	80	mA
		II		100	
$I_H$	$I_T=500\text{mA}$		MAX.	75	mA
$dV/dt$	$V_D=540\text{V}$ Gate Open $T_j=125^\circ\text{C}$		MIN.	2000	V/ $\mu\text{s}$
$(dI/dt)_c$	$(dV/dt)_c=20\text{V}/\mu\text{s } T_j=125^\circ\text{C}$		MIN.	25	A/ms
$t_{on}$	$I_G=80\text{mA } I_A=400\text{mA } I_R=40\text{mA}$ $T_j=25^\circ\text{C}$		TYP.	10	$\mu\text{s}$
$t_{off}$				70	

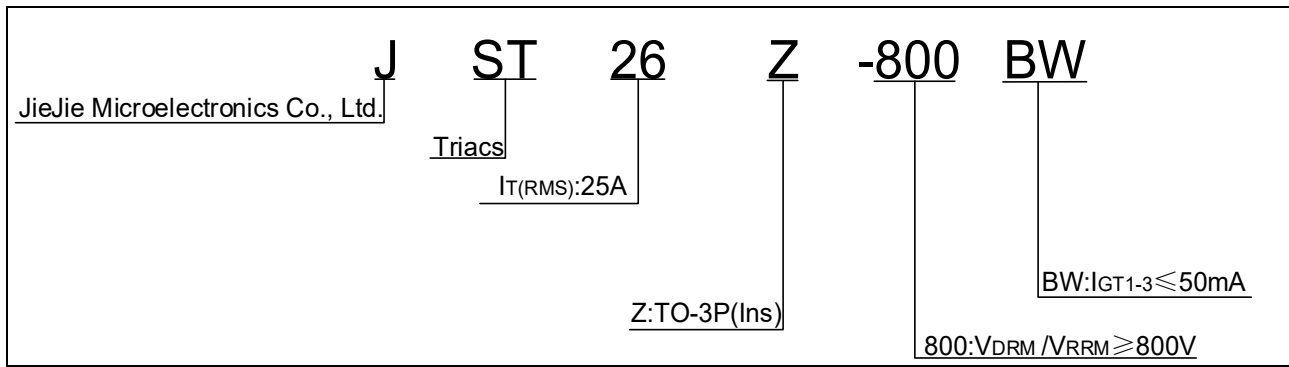
**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=35\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
$V_{TO}$	Threshold voltage	$T_j=125^\circ\text{C}$	0.73	V
$R_D$	Dynamic resistance	$T_j=125^\circ\text{C}$	25	m $\Omega$
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	$\mu\text{A}$
$I_{RRM}$		$T_j=125^\circ\text{C}$	2	mA

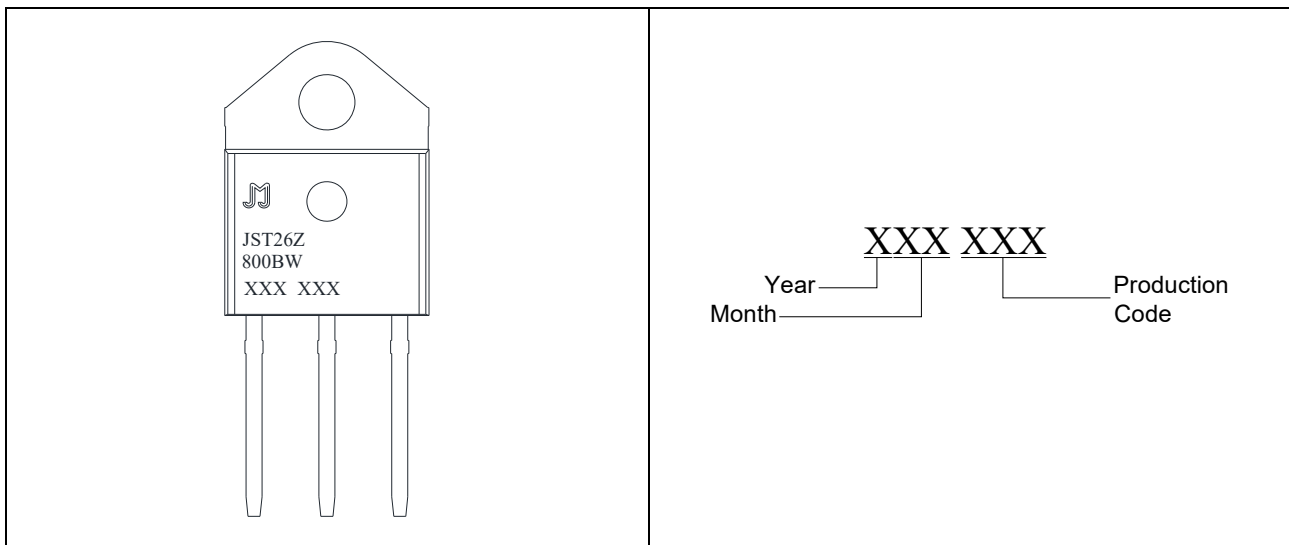
**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.1	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (AC)	50	$^\circ\text{C}/\text{W}$

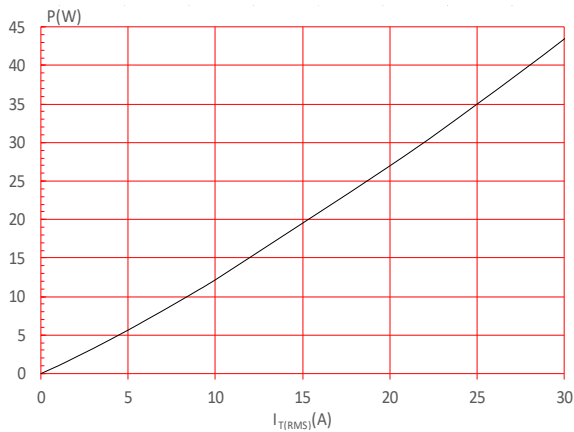
ORDERING INFORMATION



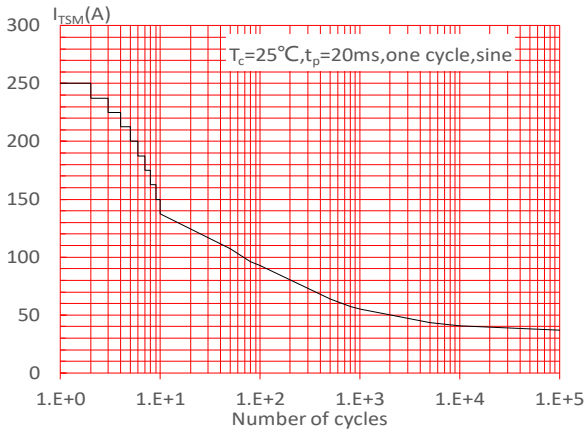
MARKING



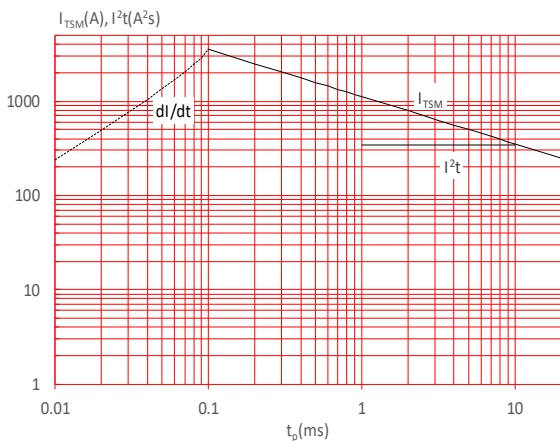
**FIG.1** Maximum power dissipation versus RMS on-state current



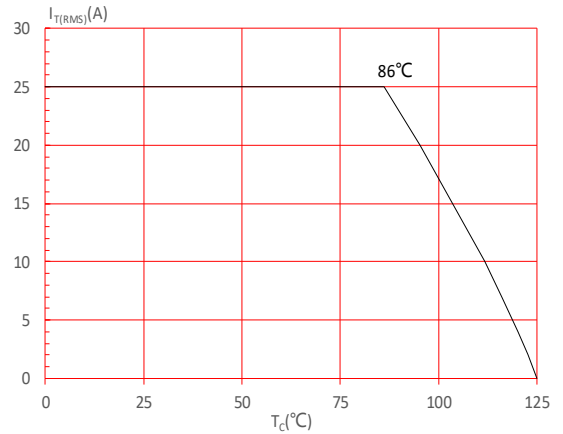
**FIG.3:** Surge peak on-state current versus number of cycles



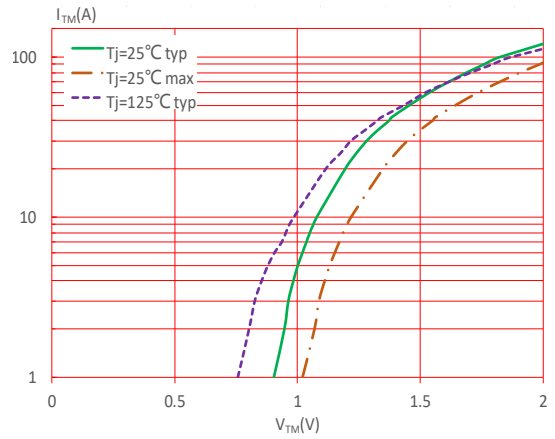
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 100\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

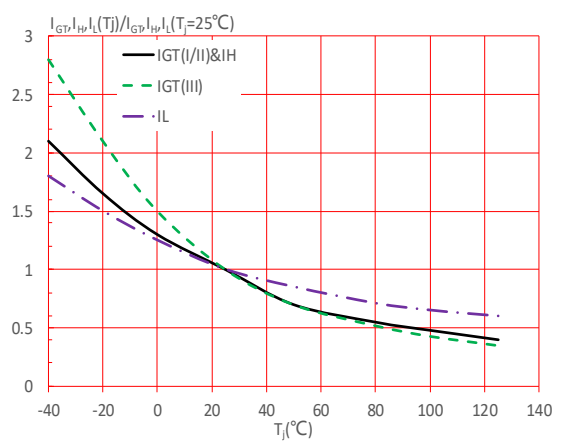
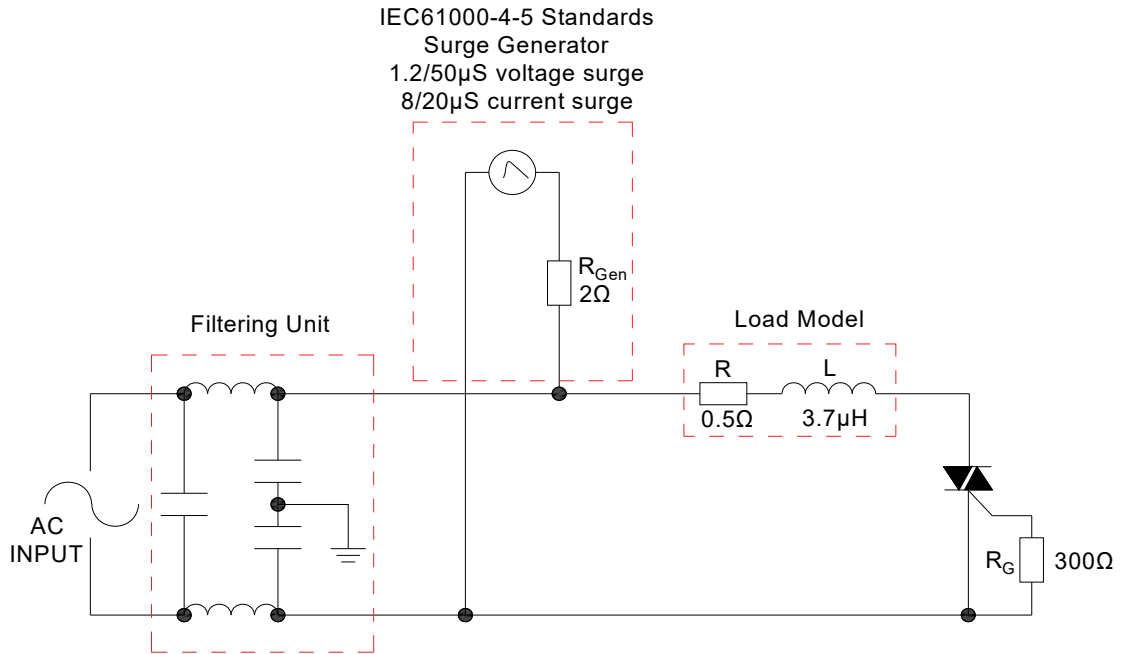


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



### SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie

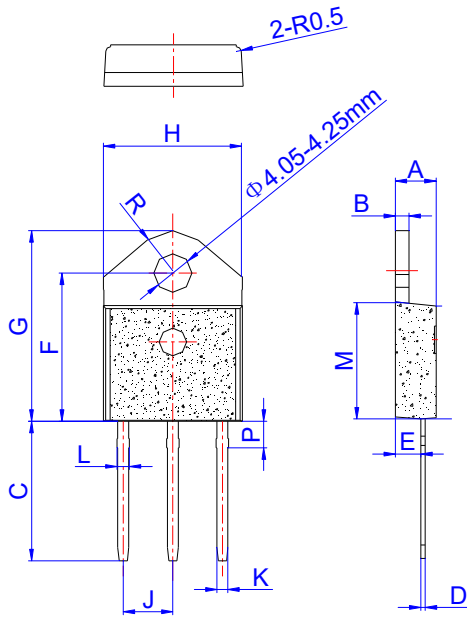
**ORDERING INFORMATION**

Order code	Voltage V <sub>DRM</sub> /V <sub>RRM</sub> (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I - II - III			
JST26Z-800BW	800	50	TO-3P(Ins)	30	Tube

**Document Revision History**

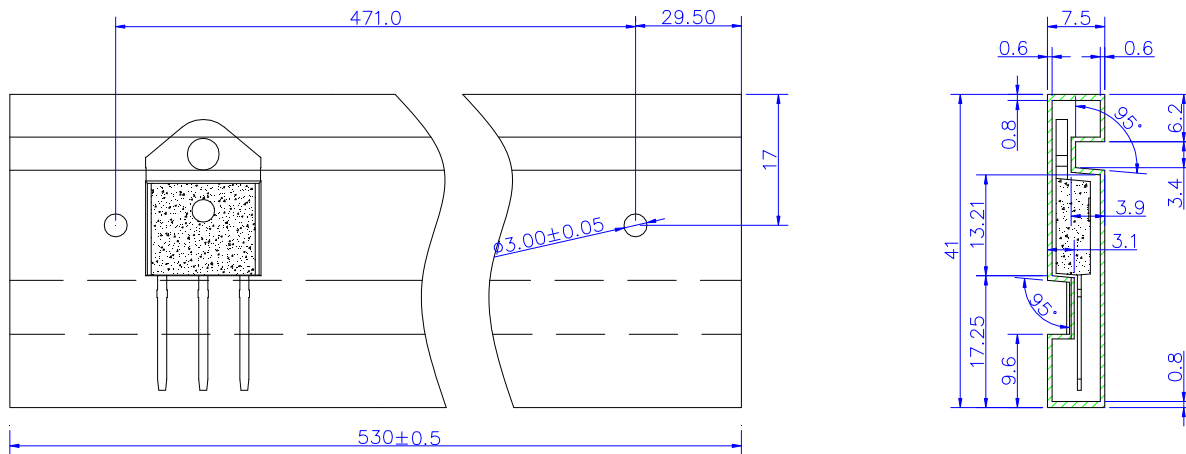
Date	Revision	Changes
Apr.12, 2023	A.1.0	Last update

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.25		1.45	0.049		0.057
M	12.37		12.77	0.487		0.503
P	2.80		3.00	0.110		0.118
R		4.35			0.171	


DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-3P	TUBE	30	450	2,250

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